

Contributors to This Issue

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CLAYTON B. BROWN, B.S.E.E., 1952, Polytechnic Institute of Brooklyn; Bell Telephone Laboratories, 1937—. Mr. Brown has been engaged in the development of central office switching apparatus and solderless wrapped connections. He is currently a supervisor at the Columbus Laboratory responsible for the development of crossbar switches and wire spring and miscellaneous relays.

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E. A. J. MARCATILI, Aeronautical Engineer, 1947, and E.E., 1948, University of Córdoba (Argentina); research staff, University of Córdoba, 1947-54; Bell Telephone Laboratories, 1954—. Mr. Marcatili has been engaged in the theory and design of filters in multimode waveguides and in wave-guide systems research. More recently he has concentrated in the study of optical transmission media. Fellow, IEEE.

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DONALD K. WILSON, B.S., 1950 and M.S., 1951, Pennsylvania State University; Ph.D., 1963, Rutgers University; Bell Telephone Laboratories, 1951-1954, 1956—. Mr. Wilson has worked on alloyed and diffused silicon diodes and transistors, measurements of bulk semicon-

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